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(71) Applicant *(for all designated States except US)*: **APPLIED MATERIALS, INC.** [US/US]; P.O. Box 450A, Santa Clara, California 95052 (US).

(72) Inventors; and

(75) Inventors/Applicants *(for US only)*: **INGLE, Nitin, K.** [IN/US]; 633 Hudson Drive, Santa Clara, California 95051 (US). **YUAN, Zheng** [CA/US]; 42024 Benbow Drive, Fremont, California 94539 (US). **BANTHIA, Vikash** [US/US]; 825 Bourbon Ct., Mountain View, California 94041 (US). **XIA, Xinyun** [CN/US]; 687 Picasso Terrace, Sunnyvale, California 94087 (US). **FORSTNER, Hali, J. L.** [CA/US]; 2018 Arbor Avenue, Belmont, California 94002 (US). **PAN, Rong** [US/US]; 2390 Lava Drive, San Jose, California 95133 (US).

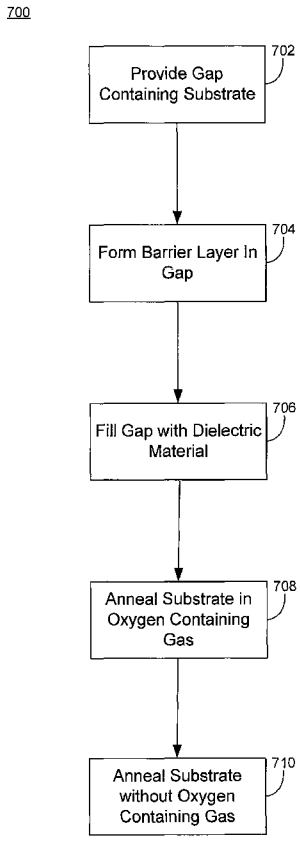
(74) Agents: **BERNARD, Eugene** et al.; Townsend and Townsend and Crew LLP, Two Embarcadero Center, Eighth Floor, San Francisco, California 94111-3834 (US).

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(54) Title: MULTI-STEP ANNEAL OF THIN FILMS FOR FILM DENSIFICATION AND IMPROVED GAP-FILL



(57) Abstract: A method of annealing a substrate that has a trench containing a dielectric material formed on a silicon nitride layer between the dielectric material and the substrate, where the method includes annealing the substrate at a first temperature of about 800°C or more in a first atmosphere comprising an oxygen containing gas, and annealing the substrate at a second temperature of about 800°C to about 1400°C in a second atmosphere lacking oxygen.

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